

### General Description

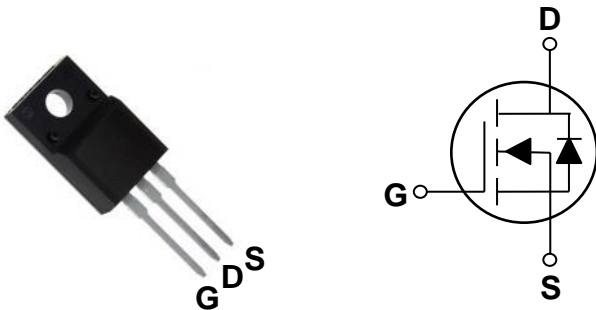
These N-Channel enhancement mode power field effect transistors are planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply

BVDSS	RDSON	ID
200V	130mΩ	20A

### Features

- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### TO220F Pin Configuration



### Applications

- High efficient switched mode power supplies
- TV Power
- Adapter/charger
- Networking
- PV Inverter / UPS



### Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	200	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	20	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	13	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	80	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	420	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	29	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	25	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.2	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	5	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	200	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =200V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =160V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =8A	---	100	130	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	3	4	5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =30V, I <sub>D</sub> =5A	---	6.5	---	S

**Dynamic and switching Characteristics**

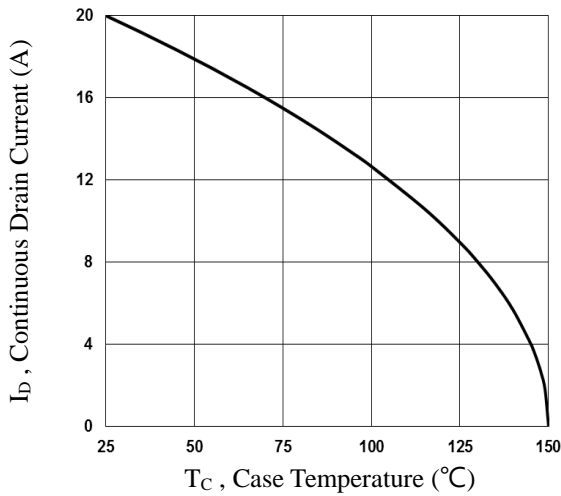
Q <sub>g</sub>	Total Gate Charge <sup>3,4</sup>	V <sub>DS</sub> =160V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A	---	30	60	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3,4</sup>		---	7.5	115	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3,4</sup>		---	11	22	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3,4</sup>	V <sub>DD</sub> =100V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =10A	---	22	44	ns
T <sub>r</sub>	Rise Time <sup>3,4</sup>		---	4	8	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3,4</sup>		---	44	88	
T <sub>f</sub>	Fall Time <sup>3,4</sup>		---	6	12	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	1330	2600	pF
C <sub>oss</sub>	Output Capacitance		---	195	380	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	21	40	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	2.3	4.6	Ω

**Drain-Source Diode Characteristics and Maximum Ratings**

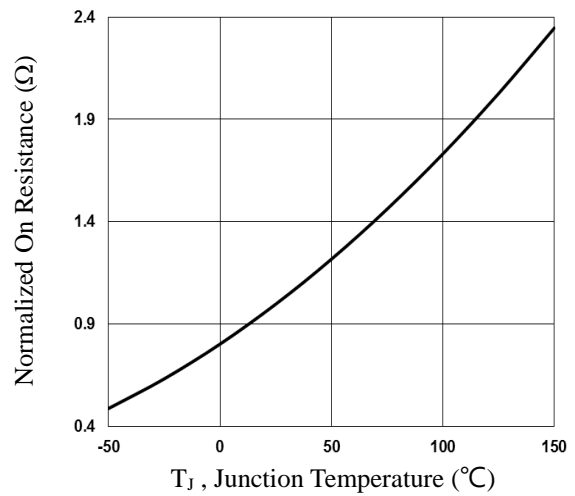
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	20	A
I <sub>SM</sub>	Pulsed Source Current		---	---	40	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time <sup>3</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =10A, dI/dt=100A/μs	---	125	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge <sup>3</sup>	T <sub>J</sub> =25°C	---	610	---	nC

Note :

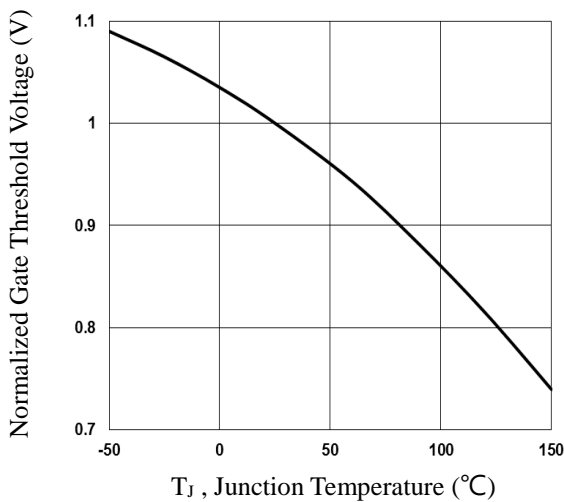
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, L=1mH, I<sub>AS</sub>=29A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



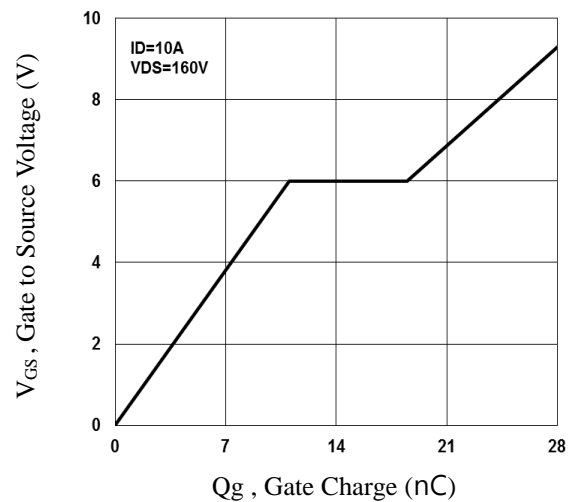
**Fig.1 Continuous Drain Current vs. T<sub>c</sub>**



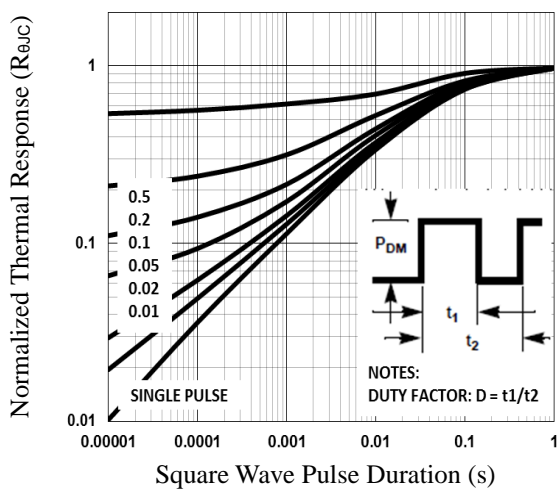
**Fig.2 Normalized R<sub>DS(on)</sub> vs. T<sub>j</sub>**



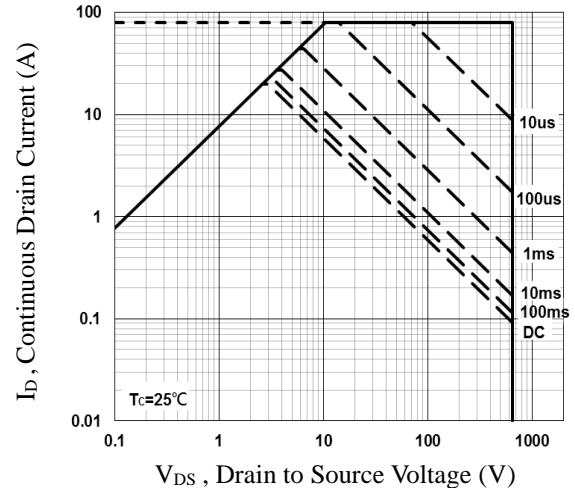
**Fig.3 Normalized V<sub>th</sub> vs. T<sub>j</sub>**



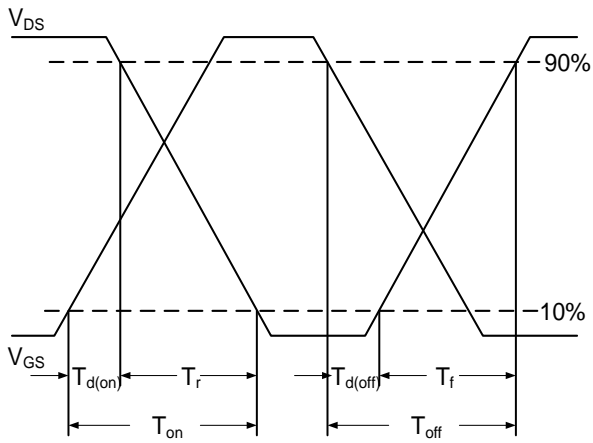
**Fig.4 Gate Charge Waveform**



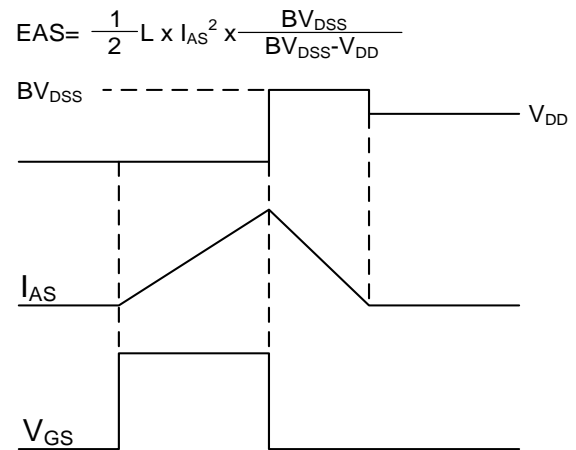
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**



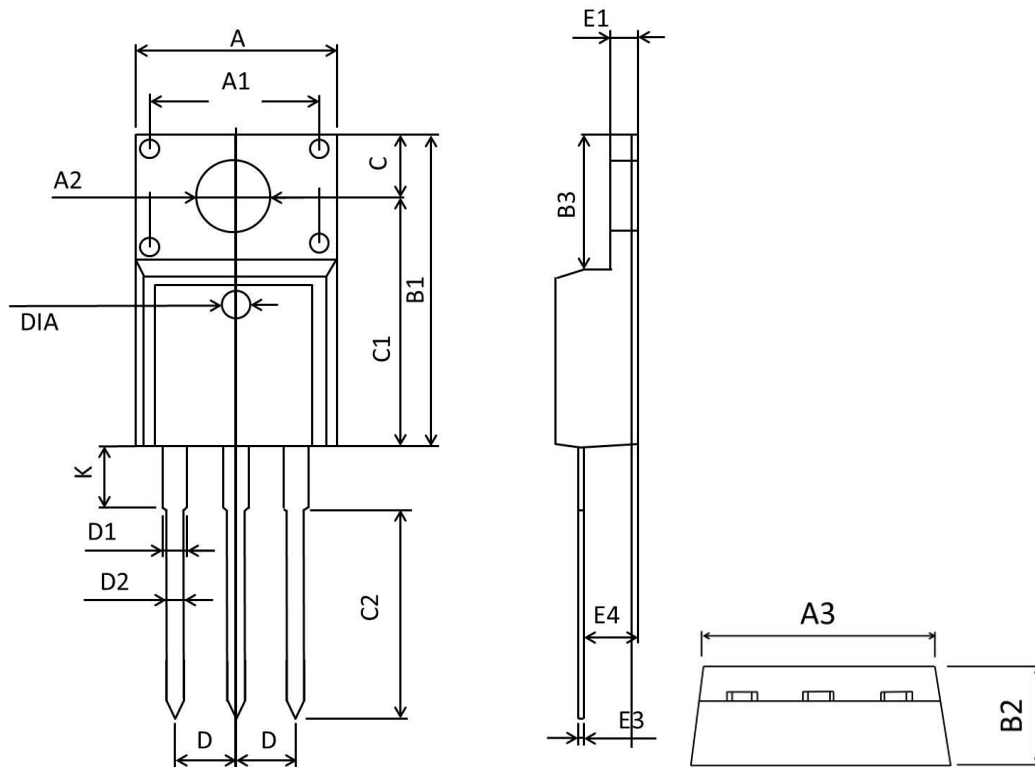
**Fig.7 Switching Time Waveform**



**Fig.8 EAS Waveform**



**TO220F PACKAGE INFORMATION**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	9.860	10.460	0.389	0.411
A1	6.900	7.100	0.272	0.279
A2	3.100	3.500	0.123	0.137
B1	9.500	9.900	0.375	0.389
B2	4.500	4.900	0.178	0.192
B3	6.480	6.880	0.256	0.271
C	3.100	3.500	0.123	0.137
C1	12.270	12.870	0.484	0.506
C2	12.580	13.380	0.496	0.526
D	2.490	2.590	0.099	0.101
D1	1.070	1.470	0.043	0.057
D2	0.700	0.900	0.028	0.035
K	2.900	3.300	0.115	0.129
E1	2.340	2.740	0.093	0.107
E3	0.400	0.600	0.016	0.023
E4	2.560	2.960	0.101	0.116
DIA	1.45	1.55	0.058	0.061